
2SA1031, 2SA1032

Silicon PNP Epitaxial

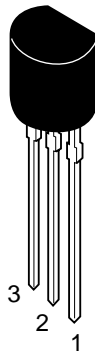
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Application

- Low frequency low noise amplifier
- Complementary pair with 2SC458 (LG) and 2SC2310

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1031, 2SA1032

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

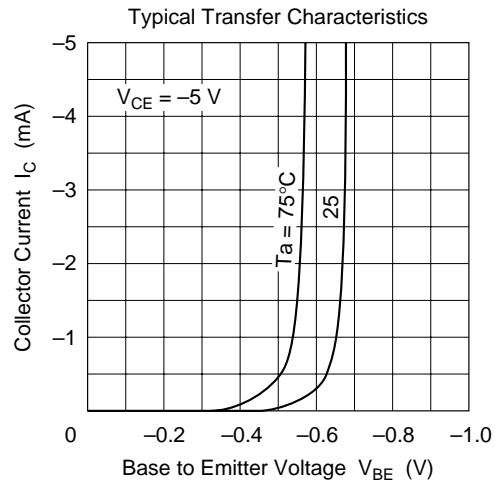
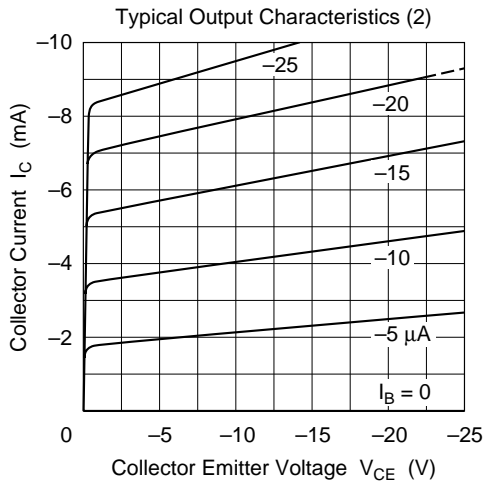
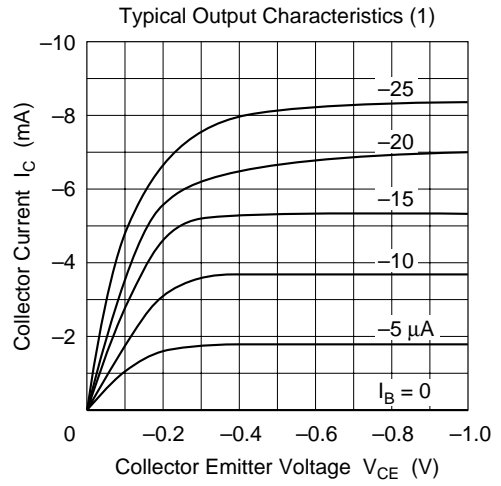
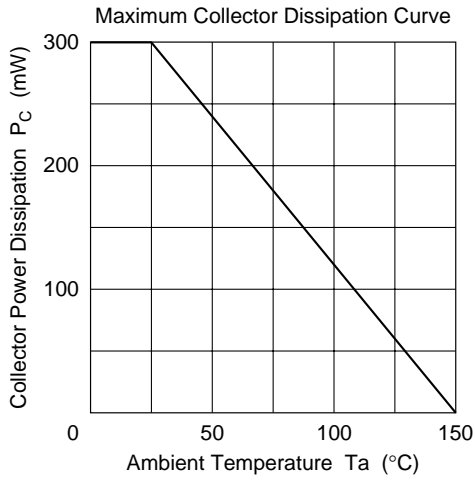
Item	Symbol	2SA1031	2SA1032	Unit
Collector to base voltage	V_{CBO}	-30	-55	V
Collector to emitter voltage	V_{CEO}	-30	-50	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_{C}	-100	-100	mA
Emitter current	I_{E}	100	100	mA
Collector power dissipation	P_{C}	300	300	mW
Junction temperature	T_{j}	150	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	-55 to +150	$^\circ\text{C}$

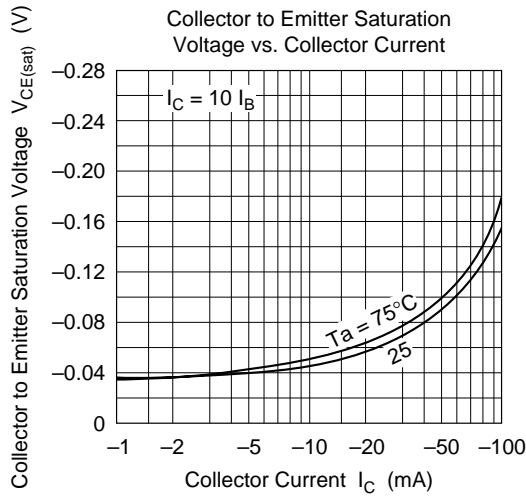
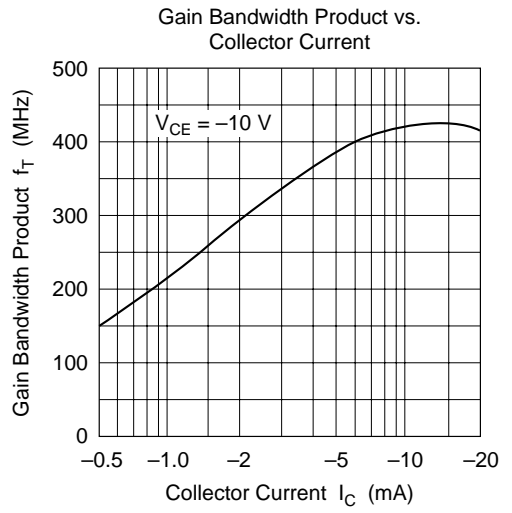
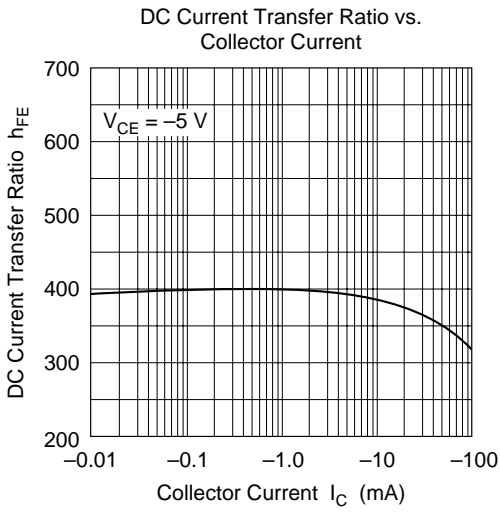
Electrical Characteristics (Ta = 25°C)

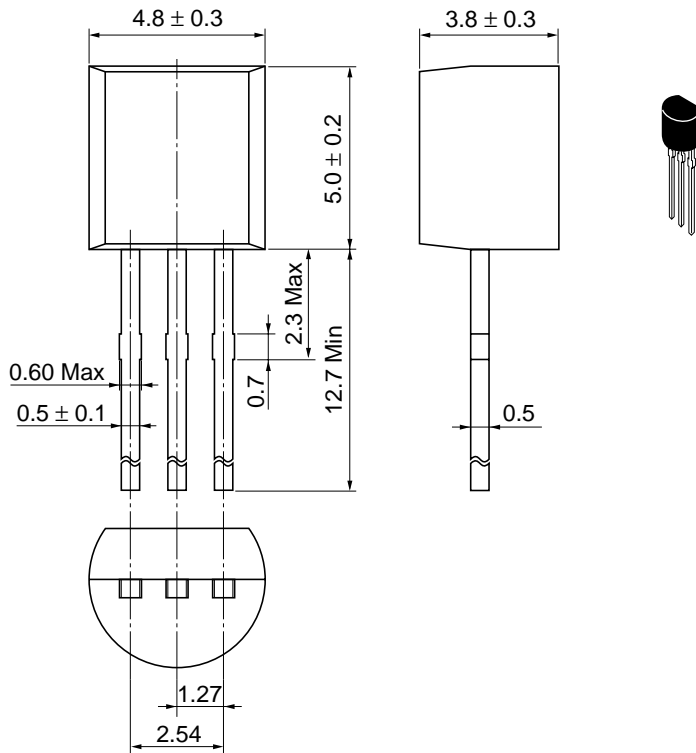
Item	Symbol	2SA1031			2SA1032			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-30	—	—	-55	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-30	—	—	-50	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.5	—	—	-0.5	μA	$V_{CB} = -18 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.5	—	—	-0.5	μA	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500	100	—	320		$V_{CE} = -12 \text{ V},$ $I_C = -2 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-0.8	—	—	-0.8	V	$V_{CE} = -12 \text{ V},$ $I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	—	—	-0.2	V	$I_C = -10 \text{ mA},$ $I_B = -1 \text{ mA}$
Gain bandwidth product	f_T	200	280	—	200	280	—	MHz	$V_{CE} = -12 \text{ V},$ $I_C = -2 \text{ mA}$
Collector output capacitance	Cob	—	3.3	4.0	—	3.3	4.0	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ $f = 1 \text{ MHz}$
Noise figure	NF	—	—	5	—	—	5	dB	$V_{CE} = -6 \text{ V},$ $I_C = -0.1 \text{ mA},$ $R_g = 500 \Omega,$ $f = 120 \text{ Hz}$

Note: 1. The 2SA1031 and 2SA1032 are grouped by h_{FE} as follows.

	B	C	D
2SA1031	100 to 200	160 to 320	250 to 500
2SA1032	100 to 200	160 to 320	—







Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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